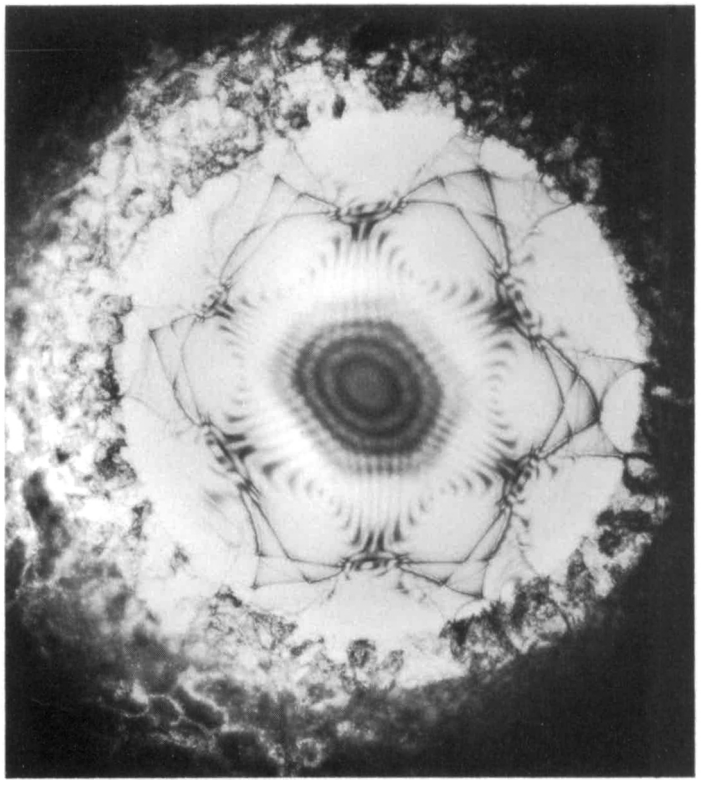
EDITOR'S CHOICE

Figures appearing in the EDITOR'S CHOICE are those arising from materials research which strike the editor's fancy as being aesthetically appealing and eye-catching. No further criteria are applied and none should be assumed. When taken out of context, such figures often evoke images beyond and unrelated to the original meaning. Submissions of candidate figures are welcome and should include a complete source citation, a photocopy of the report in which it appears (or will appear), and a reproduction-quality original drawing or photograph of the figure in question.



Our EDITOR'S CHOICE for this issue is another example of nature imitating nature with the help of the electron microscope. This sixfold symmetric flower is a bright-field transmission electron micrograph of a (111) zone-axis pattern in a single-crystal silicon membrane only 2,800 angstroms thin. The crystal is viewed through a hole in a reacted overlayer of nickel monosilicide. The strains in the silicon which manifest as the distorted flower image arise from the action of stresses in the surrounding overlayer. A full account of this work can be found in "Nickel Silicide Growth on Single-Crystal Silicon Membranes" by P. Hren, A. Fernandez and J. Silcox (Mater. Res. Soc. Symp. Proc. **102**, Pittsburgh, PA, 1988) in which a similar figure of slightly greater magnification and less complete flower analogy appears. □

ERRATA:

The description of the March 1988 cover incorrectly reads in reverse of the photo. The description should have read as follows: The KrF laser light is incident from the lower left onto the target superconductor (held inside the copper ring shown at right center). The "plume" of superconducting material is deposited on the substrate at the left facing the pellet. (The glow further to the left is from scattered excimer laser light striking the back of the substrate holder.)

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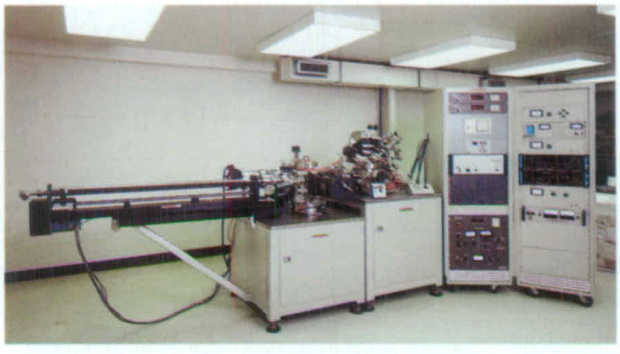

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